

ES1PB, ES1PC & ES1PD

New Product

t Vishay General Semiconductor

High Current Density Surface Mount Ultrafast Rectifiers



DO-220AA (SMP)

FEATURES

- Very low profile typical height of 1.0 mm
- Ideal for automated placement
- Glass passivated chip junction
- Ultrafast recovery times for high efficiency
- Low forward voltage, low power losses
- Low thermal resistance
- Meets MSL level 1 per J-STD-020C, LF max peak of 260 °C
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC

TYPICAL APPLICATIONS

For use in secondary rectification and free-wheeling for ultrafast switching speeds of ac-to-dc and dc-to-dc converters for both consumer and automotive applications.

MECHANICAL DATA

Case: DO-220AA (SMP)

Epoxy meets UL 94V-0 flammability rating

Terminals: Matte tin plated leads, solderable per J-STD-002B and JESD22-B102D

E3 suffix for commercial grade, HE3 suffix for high reliability grade

Polarity: Color band denotes the cathode end

MAXIMUM RATINGS ($T_A = 25$ °C unless otherwise noted)					
PARAMETER	SYMBOL	ES1PB	ES1PC	ES1PD	UNIT
Device marking code		EB	EC	ED	
Maximum repetitive peak reverse voltage	V _{RRM}	100	150	200	V
Maximum average forward rectified current (see Fig. 1)	I _{F(AV)}	1.0		А	
Peak forward surge current 10 ms single half sine-wave superimposed on rated load	I _{FSM}	30		А	
Operating junction and storage temperature range	T _J , T _{STG}	- 55 to + 150 °C		°C	

ELECTRICAL CHARACTERISTICS (T _A = 25 °C unless otherwise noted)					
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT	
Maximum instantaneous forward voltage	at I _F = 0.6 A, T _j = 25 °C at I _F = 1 A, T _j = 25 °C	V _F	0.865 0.920	V	
Maximum reverse current at rated $V_R^{(1)}$	$T_{j} = 25 °C$ $T_{j} = 125 °C$	I _R	5.0 500	μΑ	
Maximum reverse recovery time	at $I_F = 0.5 \text{ A}, I_R = 1 \text{ A}, I_{rr} = 0.25 \text{ A}$	t _{rr}	15	ns	

MAJOR RATINGS AND CHARACTERISTICS Image: line with the system Image: line with the system VRRM 100 V, 150 V, 200 V trr 15 ns VF 0.92 V Ti max. 150 °C

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ELECTRICAL CHARACTERISTICS (T _A = 25 °C unless otherwise noted)						
PARAMETER	TEST CONDITIONS SYMBOL		VALUE	UNIT		
Typical reverse recovery time	at $I_F = 1.0 \text{ A}$, $V_R = 30 \text{ V}$ di/dt = 50 A/µs, $I_{rr} = 10 \% I_{RM} T_j = 25 \degree C$ at $I_F = 1.0 \text{ A}$, $V_R = 30 \text{ V}$ di/dt = 50 A/µs, $I_{rr} = 10 \% I_{RM} T_j = 100 \degree C$	t _{rr}	25 30	ns		
Typical reverse recovery time	at $I_F = 1.0 \text{ A}$, $V_R = 30 \text{ V}$ di/dt = 50 A/µs, $I_{rr} = 10 \% I_{RM} T_j = 25 \degree C$ at $I_F = 1.0 \text{ A}$, $V_R = 30 \text{ V}$ di/dt = 50 A/µs, $I_{rr} = 10 \% I_{RM} T_j = 100 \degree C$	Q _{RR}	8 10	nC		
Typical junction capacitance	at 4.0 V, 1 MHz	CJ	10	pF		

Note:

(1) Pulse test: 300 μs pulse width, 1 % duty cycle

THERMAL CHARACTERISTICS (T _A = 25 °C unless otherwise noted)					
PARAMETER	SYMBOL	ES1PB	ES1PC	ES1PD	UNIT
	$R_{ ext{ heta}JA}$	105			°C/W
Typical thermal resistance ⁽¹⁾	$R_{\theta JL}$	15			
	$R_{ ext{ heta}JC}$		20		

Note:

(1) Thermal resistance from junction to ambient and junction to lead mounted on P.C.B. with 5.0 x 5.0 mm copper pad areas. $R_{\theta JL}$ is measured at the terminal of cathode band. $R_{\theta JC}$ is measured at the top centre of the body

ORDERING INFORMATION					
PREFERRED P/N	UNIT WEIGHT (g)	PREFERRED PACKAGE CODE	BASE QUANTITY	DELIVERY MODE	
ES1PB-E3/84A	0.024	84A	3000	7" Diameter Plastic Tape & Reel	
ES1PB-E3/85A	0.024	85A	10000	13" Diameter Plastic Tape & Reel	

RATINGS AND CHARACTERISTICS CURVES

(T_A = 25 °C unless otherwise noted)

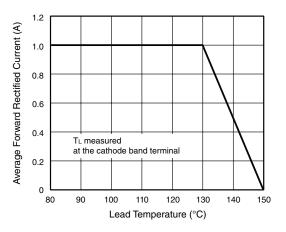


Figure 1. Maximum Forward Current Derating Curve

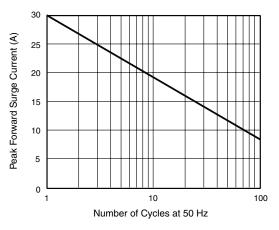


Figure 2. Maximum Non-Repetitive Peak Forward Surge Current



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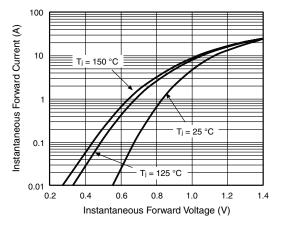
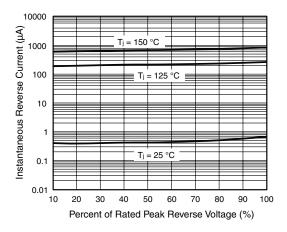


Figure 3. Typical Instantaneous Forward Characteristics





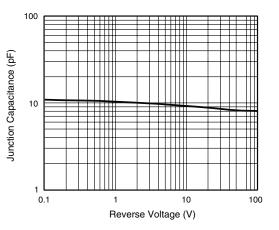
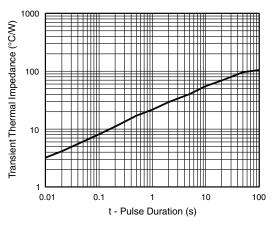
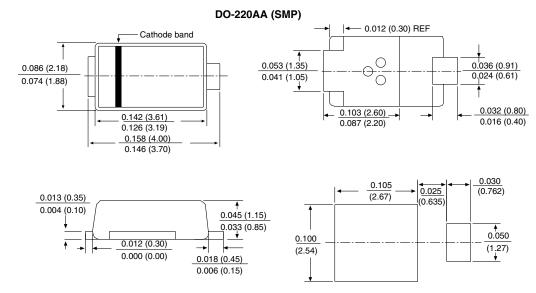


Figure 5. Typical Junction Capacitance





PACKAGE OUTLINE DIMENSIONS in inches (millimeters)





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